

supplying etching gas to the plasma etching reactor and energizing the etching gas into a plasma state, the etching gas including at least one fluorocarbon reactant and at least one oxygen reactant supplied to the plasma etching reactor at a flow rate ratio of oxygen reactant to fluorocarbon reactant of 1.5 or less;

C1  
cont  
etching exposed portions of the silicon nitride layer with the plasma so as to etch openings in the silicon nitride layer with the plasma while providing an etch rate selectivity of the etching rate of the silicon nitride layer to the etching rate of the dielectric layer of at least about 10.

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